L Number	Hits	Search Text	DB	Time stamp
-	227	438/658.ccls.	USPAT	2004/04/20
_	137	438/658.ccls. and conductive	USPAT	11:39 2003/11/18
-	136	438/658.ccls. and conductive and layer	USPAT	10:36 2003/11/18
-	68	438/658.ccls. and conductive and layer and via	USPAT	10:37 2003/11/18 10:37
-	31	438/658.ccls. and conductive and layer and via and electromigration	USPAT	2003/11/18 10:37
_	5	438/658.ccls. and conductive and layer and via and electromigration and dopant	USPAT	2003/11/18
-	1	438/658.ccls. and conductive and layer and via and electromigration and dopant	USPAT	2003/11/18
	2	and aluminum and concentrat\$4 and atomic 438/658.ccls. and conductive and layer	USPAT	2003/11/18
	2	and via and electromigration and dopant and aluminum and concentrat\$4	OSPAI	12:27
-	5	438/658.ccls. and conductive and layer and via and electromigration and dopant	USPAT	2003/11/24 11:49
		and aluminum		
-	51	438/658.ccls. and "conductive layer"	USPAT	2003/11/21 14:11
-	50	438/658.ccls. and "conductive layer" and substrate	USPAT	2003/11/21
-	21	438/658.ccls. and "conductive layer" and substrate and "dielectric layer"	USPAT	2003/11/21
_	15	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and	USPAT	2003/11/21 14:11
		"barrier layer"		
_	12	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and	USPAT	2003/11/21 14:12
-	0	"barrier layer" and via 438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and	USPAT	2003/11/21 14:12
_	6	"barrier layer" and via and dopant 438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and	USPAT	2003/11/21 14:14
_	6	"barrier layer" and via and dop\$4 438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
		substrate and "dielectric layer" and "barrier layer" and via and dop\$4 and		14:15
-	2	electromigration 438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
		substrate and "dielectric layer" and "barrier layer" and via and dop\$4 and electromigration and atomic		15:19
_	0	438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and	USPAT	2003/11/21 15:19
		"barrier layer" and via and dop\$4 and electromigration and atomic and implant		13.13
_	2	438/658.ccls. and conductive and layer and via and electromigration and dopant	USPAT	2003/11/24 11:49
		and aluminum and ion	IICD»	2003/11/24
-	2	438/658.ccls. and conductive and layer and via and electromigration and dopant and aluminum and ion and gas	USPAT	11:50
_	4	(("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.	USPAT	2004/04/20 11:40
_	3	((("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.) and	USPAT	2004/04/20 12:11
	2	conduct\$4 and dielectric ((("5614764") or ("5904560") or	USPAT	2004/04/20
-	2	((("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.) and conduct\$4 and dielectric and via	USPAI	12:17
_	0	((("5614764") or ("5904560") or	USPAT	2004/04/20
		("5909635") or ("6191029")).PN.) and conduct\$4 and dielectric and via and etch		12:18
		and ion	L	

-	1	((("5614764") or ("5904560") or	USPAT	2004/04/20
		("5909635") or ("6191029")).PN.) and		14:16
		conduct\$4 and dielectric and via and etch		
-	0	438/658.	USPAT	2004/04/20
				14:16
_	235	438/658.ccls.	USPAT	2004/04/20
	230	1007 000100101		14:17
_	50	438/658.ccls. and substrate and conduct\$4	USPAT	2004/04/20
	30	and dielectric and via	USPAI	14:18
	2.5		IIG D D III	
_	35	438/658.ccls. and substrate and conduct\$4	USPAT	2004/04/20
		and dielectric and via and tin		14:29
-	23	438/658.ccls. and substrate with	USPAT	2004/04/20
		conduct\$4 and dielectric and via and tin		15:03
-	3	438/658.ccls. and substrate with	USPAT	2004/04/29
		conduct\$4 with barrier and dielectric and		10:18
		via and tin		
-	0	subbstrate with conduct\$4 with barrier	USPAT	2004/04/21
		and dielectric and via and tin		09:21
_	418	substrate with conduct\$4 with barrier and	USPAT	2004/04/21
		dielectric and via and tin		09:43
-	2	substrate with conduct\$4 with barrier and	USPAT	2004/04/21
	_	dielectric and via and tin and		09:43
1		electronmigration		
l _	142	substrate with conduct\$4 with barrier and	USPAT	2004/04/21
1 -	147	dielectric and via and tin and	551711	09:44
		electromigration		00.33
	٥-		USPAT	2004/04/29
-	95	438/658.ccls. and conduct\$4 with	USPAI	
		substrate	IICDAE	10:20
-	87	438/658.ccls. and conduct\$4 with	USPAT	2004/04/29
	.	substrate and (dielectric or oxide)		10:21
-	49	438/658.ccls. and conduct\$4 with	USPAT	2004/04/29
		substrate and (dielectric or oxide) and]	10:21
		via		
-	19	438/658.ccls. and conduct\$4 with	USPAT	2004/04/29
		substrate and (dielectric or oxide) and		10:21
		via and (dopant or impur\$4)		
-	10	438/658.ccls. and conduct\$4 with	USPAT	2004/04/29
		substrate and (dielectric or oxide) and		10:22
		via and (dopant or impur\$4) and barrier		
_	1	438/658.ccls. and conduct\$4 with	USPAT	2004/04/29
		substrate and (dielectric or oxide) and		10:22
		via and (dopant or impur\$4) and barrier		
		and ion and implant\$4 and gas and trench		
	2	438/658.ccls. and conduct\$4 with	USPAT	2004/04/29
_	2		ODENT	10:34
		substrate and (dielectric or oxide) and		10.34
		via and (dopant or impur\$4) and barrier		
1	_	and ion and implant\$4 and gas		0004/04/00
-	3	438/658.ccls. and conduct\$4 with	USPAT	2004/04/29
		substrate and (dielectric or oxide) and		10:36
ļ		via and (dopant or impur\$4) and barrier		
		and ion and implant\$4		
l -	7	438/658.ccls. and conduct\$4 with	USPAT	2004/04/29
		substrate and (dielectric or oxide) and		10:44
		via and (dopant or impur\$4) and barrier		
		and ion		